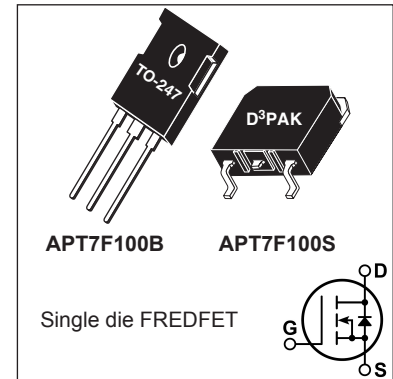**POWER PRODUCTS GROUP**

1000V, 7A, 2.0Ω Max

N-Channel FREDFET

POWER MOS 8® is a high speed, high voltage N-channel switch-mode power MOSFET. This 'FREDFET' version has a drain-source (body) diode that has been optimized for high reliability in ZVS phase shifted bridge and other circuits through reduced t_{rr}, soft recovery, and high recovery dv/dt capability. Low gate charge, high gain, and a greatly reduced ratio of C_{rss}/C_{iss} result in excellent noise immunity and low switching loss. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control di/dt during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency.

APT7F100B   **APT7F100S**

Single die FREDFET

FEATURES

- **Fast switching with low EMI**
- **Low t_{rr} for high reliability**
- **Ultra low C_{rss} for improved noise immunity**
- **Low gate charge**
- **Avalanche energy rated**
- **RoHS compliant**

TYPICAL APPLICATIONS

- **ZVS phase shifted and other full bridge**
- **Half bridge**
- **PFC and other boost converter**
- **Buck converter**
- **Single and two switch forward**
- **Flyback**

Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
I_D	Continuous Drain Current @ T_C = 25°C	7	A
	Continuous Drain Current @ T_C = 100°C	5	
I_{DM}	Pulsed Drain Current ①	27	
V_{GS}	Gate-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy ②	415	mJ
I_{AR}	Avalanche Current, Repetitive or Non-Repetitive	4	A

Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
P_D	Total Power Dissipation @ T_C = 25°C			290	W
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.43	°C/W
$R_{\theta CS}$	Case to Sink Thermal Resistance, Flat, Greased Surface		0.15		
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55		150	°C
T_L	Soldering Temperature for 10 Seconds (1.6mm from case)			300	
W_T	Package Weight		0.22		oz
			6.2		g
Torque	Mounting Torque (TO-247 Package), 6-32 or M3 screw			10	in·lbf
				1.1	N·m

050-8166 Rev B 05-2009

Static Characteristics T_J = 25°C unless otherwise specified   APT7F100B_S

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250µA		1000			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D = 250µA			1.15		V/°C
$R_{DS(on)}$	Drain-Source On Resistance ③	V_{GS} = 10V, I_D = 4A			1.76	2.0	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 0.5mA		2.5	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient				-10		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 1000V	T_J = 25°C			250	µA
		V_{GS} = 0V	T_J = 125°C			1000	
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V				±100	nA

Dynamic Characteristics T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g_{fs}	Forward Transconductance	V_{DS} = 50V, I_D = 4A		7.5		S
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 25V f = 1MHz		1800		pF
C_{rss}	Reverse Transfer Capacitance			25		
C_{oss}	Output Capacitance			158		
$C_{o(cr)}$ ④	Effective Output Capacitance, Charge Related	V_{GS} = 0V, V_{DS} = 0V to 670V		65		
$C_{o(er)}$ ⑤	Effective Output Capacitance, Energy Related			33		
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, I_D = 4A, V_{DS} = 500V		58		nC
Q_{gs}	Gate-Source Charge			10		
Q_{gd}	Gate-Drain Charge			27		
$t_{d(on)}$	Turn-On Delay Time	**Resistive Switching** V_{DD} = 670V, I_D = 4A R_G = 10Ω ⑥, V_{GG} = 15V		24		ns
t_r	Current Rise Time			26		
$t_{d(off)}$	Turn-Off Delay Time			77		
t_f	Current Fall Time			22		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions			Min	Typ	Max	Unit
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode)					7	A
I_{SM}	Pulsed Source Current (Body Diode) ①						27	
V_{SD}	Diode Forward Voltage	I_{SD} = 4A, T_J = 25°C, V_{GS} = 0V					1.2	V
t_{rr}	Reverse Recovery Time	I_{SD} = 4A ③ di_{SD}/dt = 100A/µs V_{DD} = 100V	T_J = 25°C			133	152	ns
			T_J = 125°C			209	251	
Q_{rr}	Reverse Recovery Charge		T_J = 25°C			.56		µC
			T_J = 125°C			1.2		
I_{rrm}	Reverse Recovery Current		T_J = 25°C			7		A
			T_J = 125°C			9		
dv/dt	Peak Recovery dv/dt	I_{SD} ≤ 4A, di/dt ≤1000A/µs, V_{DD} = 500V, T_J = 125°C					25	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at T_J = 25°C, L = 53mH, R_G = 25Ω, I_{AS} = 4A.

③ Pulse test: Pulse Width < 380µs, duty cycle < 2%.

④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$.

⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as C_{OSS} with V_{DS} = 67% of $V_{(BR)DSS}$. To calculate $C_{o(er)}$ for any value of V_{DS} less than $V_{(BR)DSS}$, use this equation: $C_{o(er)}$ = -3.43E-8/V_{DS}^2 + 1.44E-8/V_{DS} + 5.38E-11.

⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

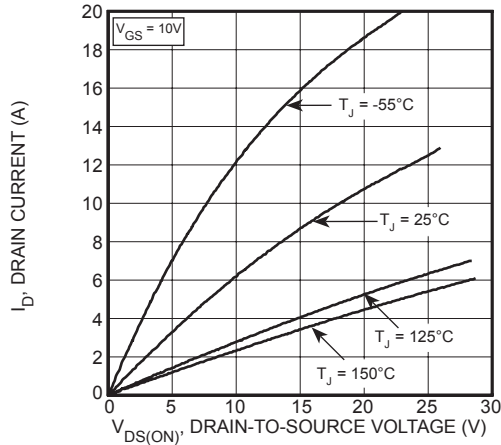**Microsemi reserves the right to change, without notice, the specifications and information contained herein.**
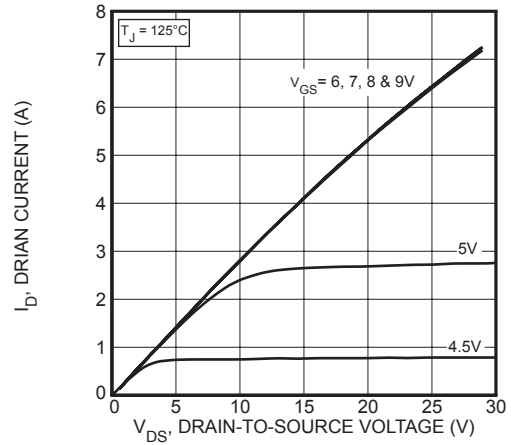
Figure 1, Output Characteristics
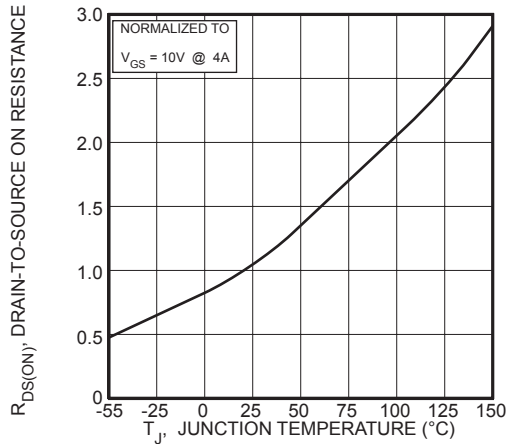

Figure 2, Output Characteristics

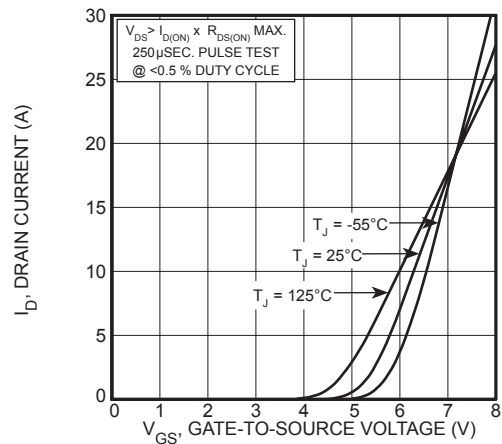**Figure 3, R$_{DS(ON)}$ vs Junction Temperature**

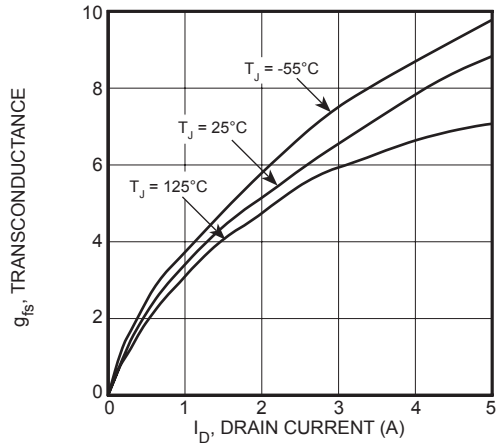**Figure 4, Transfer Characteristics**
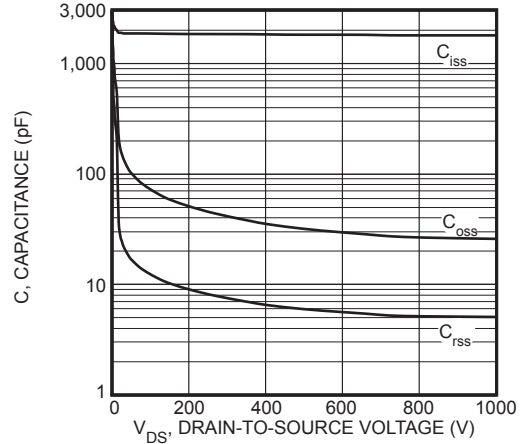

Figure 5, Gain vs Drain Current

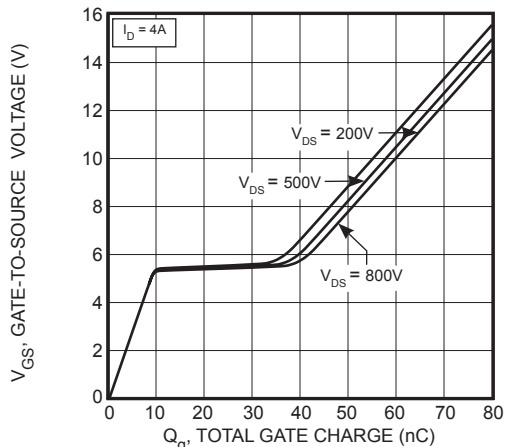**Figure 6, Capacitance vs Drain-to-Source Voltage**
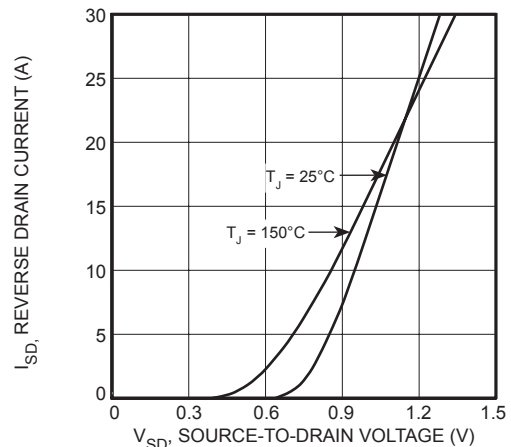

Figure 7, Gate Charge vs Gate-to-Source Voltage
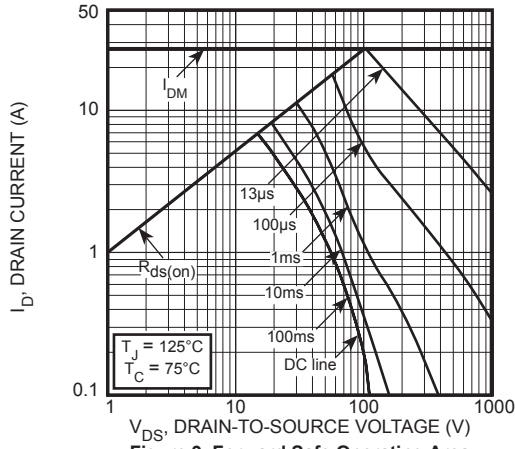

Figure 8, Reverse Drain Current vs Source-to-Drain Voltage
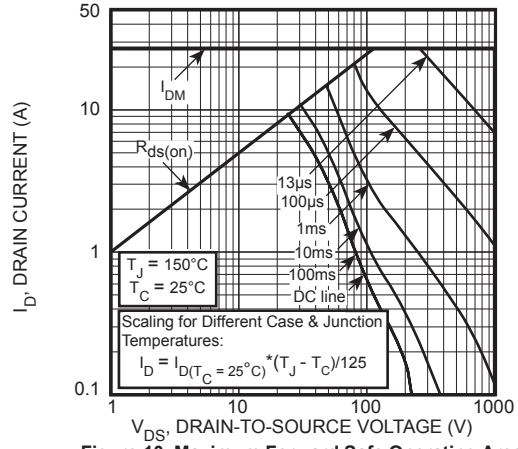
Figure 9, Forward Safe Operating Area

I_DM

R_ds(on)

$T_J = 125°C$
$T_C = 75°C$

13μs
100μs
1ms
10ms
100ms
DC line

I_D, DRAIN CURRENT (A)

V_{DS}, DRAIN-TO-SOURCE VOLTAGE (V)

Figure 10, Maximum Forward Safe Operating Area

I_DM

R_ds(on)

$T_J = 150°C$
$T_C = 25°C$

13μs
100μs
1ms
10ms
100ms
DC line

Scaling for Different Case & Junction Temperatures:

$$I_D = I_{D(T_C = 25°C)} * (T_J - T_C)/125$$

I_D, DRAIN CURRENT (A)

V_{DS}, DRAIN-TO-SOURCE VOLTAGE (V)

$Z_{\theta JC}$, THERMAL IMPEDANCE (°C/W)

D = 0.9
0.7
0.5
0.3
0.1
0.05

SINGLE PULSE

Note:

P_{DM}
t_1
t_2

t_1 = Pulse Duration
Duty Factor D = t_1/t_2
Peak $T_J = P_{DM} \times Z_{\theta JC} + T_C$
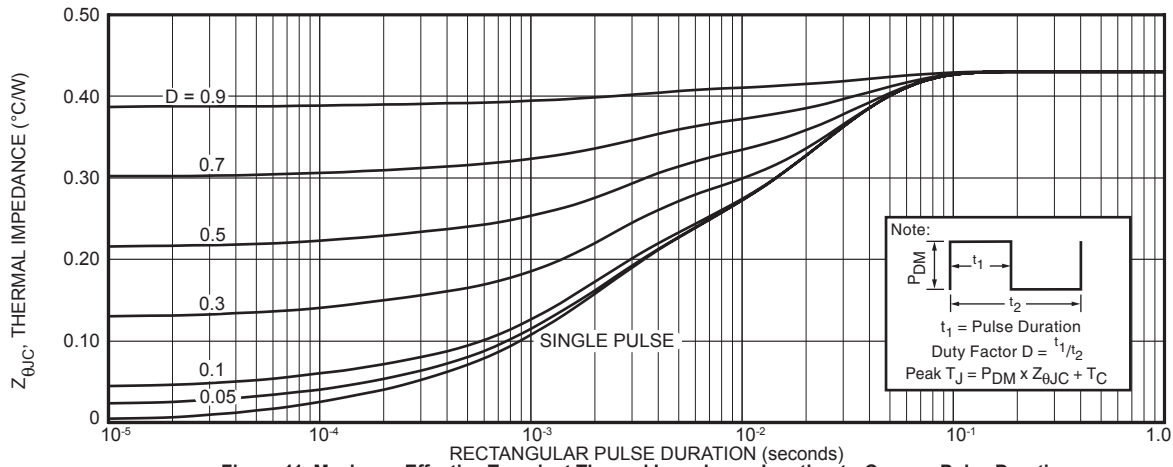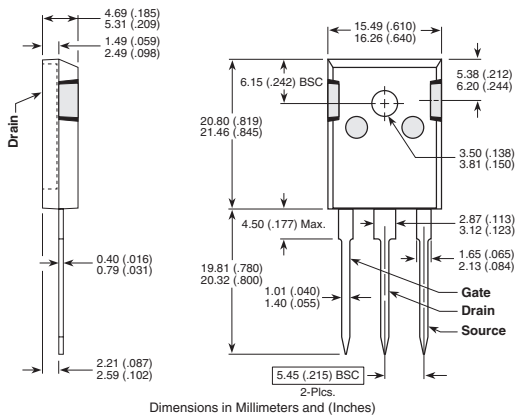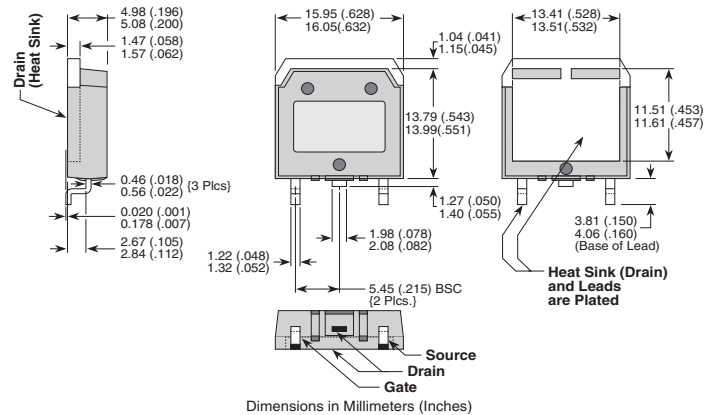
RECTANGULAR PULSE DURATION (seconds)

Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

TO-247 (B) Package Outline

D³PAK Package Outline

e1 100% Sn Plated

Drain

4.69 (.185)
5.31 (.209)

1.49 (.059)
2.49 (.098)

15.49 (.610)
16.26 (.640)

6.15 (.242) BSC

5.38 (.212)
6.20 (.244)

20.80 (.819)
21.46 (.845)

3.50 (.138)
3.81 (.150)

4.50 (.177) Max.

2.87 (.113)
3.12 (.123)

1.65 (.065)
2.13 (.084)

0.40 (.016)
0.79 (.031)

19.81 (.780)
20.32 (.800)

1.01 (.040)
1.40 (.055)

Gate
Drain
Source

2.21 (.087)
2.59 (.102)

5.45 (.215) BSC
2-Plcs.

Dimensions in Millimeters and (Inches)

Drain (Heat Sink)

4.98 (.196)
5.08 (.200)

1.47 (.058)
1.57 (.062)

0.46 (.018) {3 Plcs}
0.56 (.022)

0.020 (.001)
0.178 (.007)

2.67 (.105)
2.84 (.112)

15.95 (.628)
16.05 (.632)

1.04 (.041)
1.15 (.045)

13.79 (.543)
13.99 (.551)

1.27 (.050)
1.40 (.055)

1.98 (.078)
2.08 (.082)

1.22 (.048)
1.32 (.052)

5.45 (.215) BSC
{2 Plcs.}

Source
Drain
Gate

13.41 (.528)
13.51 (.532)

11.51 (.453)
11.61 (.457)

3.81 (.150)
4.06 (.160)
(Base of Lead)

Heat Sink (Drain)
and Leads
are Plated

Dimensions in Millimeters (Inches)

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